

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	503	257/759.ccls.	US-PGPUB; USPAT	OR	OFF	2005/08/06 18:01
L2	726	(msq (methyl adj silsesquioxane)) and ((barrier with (dielectric insulator carbide nitride oxide oxynitride)) electromigration diffusion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 18:11
L3	433	((polymeric adj alkyl adj siloxane) sicoh sioch (polymeric adj silicon adj carbide) "sic(h)") and ((barrier with (dielectric insulator carbide nitride oxide oxynitride)) electromigration diffusion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 18:21
L4	47	MIKAGI-K MIKAGI-KAORU	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/06 18:31
L5	109	((polymeric adj alkyl adj siloxane) sioch sicoh) and ((polymeric adj silicon adj carbide) "sic(h)")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 18:31
L6	58	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.) and ((polymeric adj alkyl adj siloxane) sicoh sioch (polymeric adj silicon adj carbide) "sic(h)")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 18:35
L7	471	("257"/\$.ccls. "438"/\$.ccls.) and ((polymeric adj alkyl adj siloxane) sicoh sioch sich (polymeric adj silicon adj carbide) "sic(h)")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 18:38
L8	52	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.) and ((silicon wafer semiconductor) and (damascene inlaid "in-laid") and ((copper cu) same seed same (electroplat\$3 plat43) same (cmp planar\$8)))	US-PGPUB; USPAT	OR	ON	2005/08/06 18:48
L9	58	(257/751.ccls. 257/752.ccls. 257/759.ccls. 257/760.ccls. 257/762.ccls.) and (((dielectric insulat\$4 oxide dioxide sioch sicoh sich "low-k" "low k") near4 barrier) with (reduc\$5 redox deoxid\$7))	US-PGPUB; USPAT	OR	ON	2005/08/06 18:49

L10	29	((copper cu) near2 (plat\$6 electroplat\$6)) with (seed near2 (tan tin ((tantalum titanium) adj nitride)))	US-PGPUB; USPAT	OR	ON	2005/08/06 18:51
L11	107	("5332691"   "5604158"   "5741626").PN. OR ("5821168").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/06 18:54
L12	60	((integrated adj circuit) semiconductor silicon wafer interconnect\$6) and (dielectric insulat\$6 interlayer ild oxide dioxide nitride) and (hole opening aperture via trench groove) and (sicoch sioch)).clm.	US-PGPUB	OR	ON	2005/08/06 19:00
L13	1	((integrated adj circuit) semiconductor silicon wafer interconnect\$6) and (dielectric insulat\$6 interlayer ild oxide dioxide nitride) and (hole opening aperture via trench groove) and (gett\$8 with (monolayer (atom\$6 near layer))).clm.	US-PGPUB	OR	ON	2005/08/06 19:00